LNA2W01L (LN57)

GaAs Infrared Light Emitting Diode

For optical control systems

■ Features

- High-power output, high-efficiency: $P_O = 4.5 \text{ mW (typ.)}$
- Emitted light spectrum suited for silicon photodetectors
- Infrared light emission close to monochromatic light: $\lambda_P = 950 \text{ nm}$ (typ.)
- Wide directivity: $\theta = 18^{\circ}$ (typ.)
- Ultra-miniature double ended package

■ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter | Symbol | Rating | Unit | |
|-------------------------------|------------------|-------------|------|--|
| Power dissipation | P_{D} | 75 | mW | |
| Forward current | I_{F} | 50 | mA | |
| Pulse forward current * | I_{FP} | 1 | A | |
| Reverse voltage | V_R | 3 | V | |
| Operating ambient temperature | T _{opr} | -25 to +85 | °C | |
| Storage temperature | T _{stg} | -30 to +100 | °C | |

Note) *: f = 100 Hz, Duty cycle = 0.1%

■ Electrical-Optical Characteristics $T_a = 25$ °C±3°C

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--------------------------|------------------|---|-----|------|------|------|
| Radiant power * | P _O | $I_F = 50 \text{ mA}$ | 3.0 | 4.5 | | mW |
| Reverse current | I_R | $V_R = 3 V$ | | | 10 | μА |
| Forward voltage | V_{F} | $I_F = 50 \text{ mA}$ | | 1.25 | 1.50 | V |
| Terminal capacitance | C _t | $V_R = 0 V, f = 1 MHz$ | | 35 | | pF |
| Peak emission wavelength | $\lambda_{ m P}$ | $I_F = 50 \text{ mA}$ | | 950 | | nm |
| Spectral half band width | Δλ | $I_F = 50 \text{ mA}$ | | 50 | | nm |
| Half-power angle | θ | The angle when the radiant power is halved. | | 18 | | 0 |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

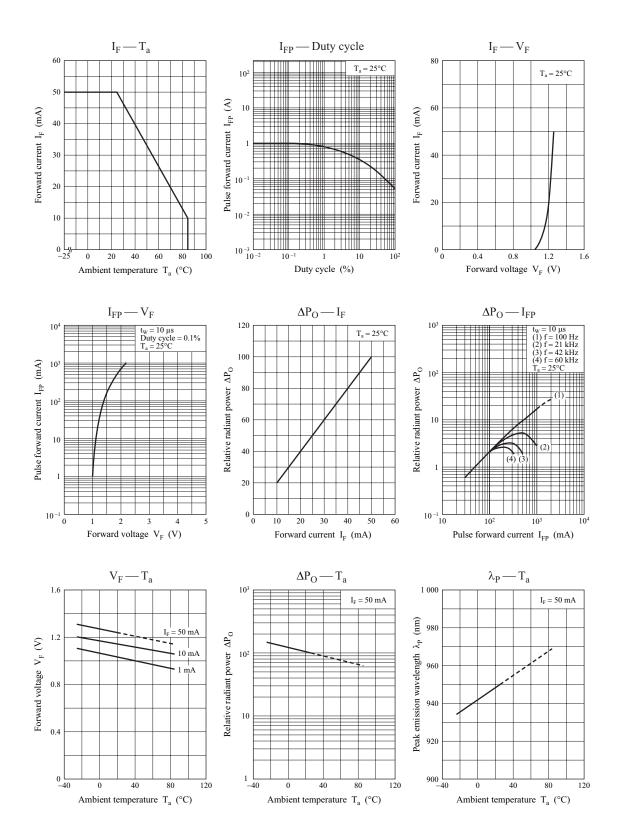
2. Cutoff frequency: 1 MHz

$$f_C: 10 \times \log \frac{P_O \text{ at } f = f_C}{P_O \text{ at } f = 50 \text{ kHz}} = -3$$

3. *: A light detection element uses a silicon diode have proofread a load with a standard device.

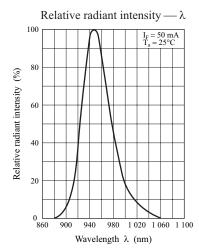
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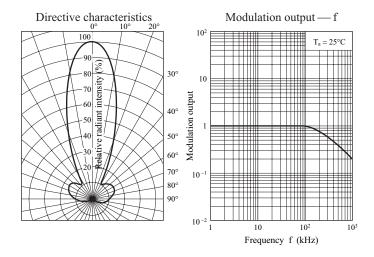
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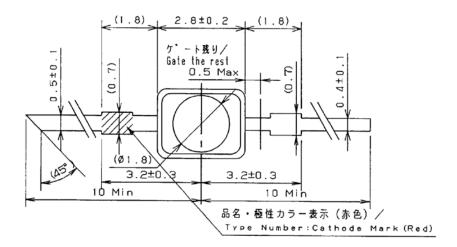


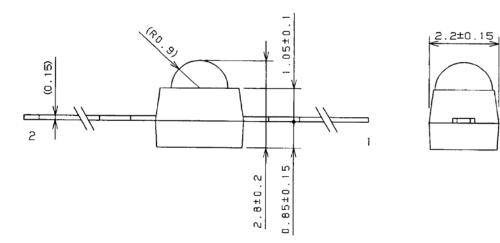
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■ Package (Unit: mm)

LETLTN2S0001





- Pin name
 - 1: Anode
 - 2: Cathode

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